Fig. 1. Core-shell acthecture for UVC LED.

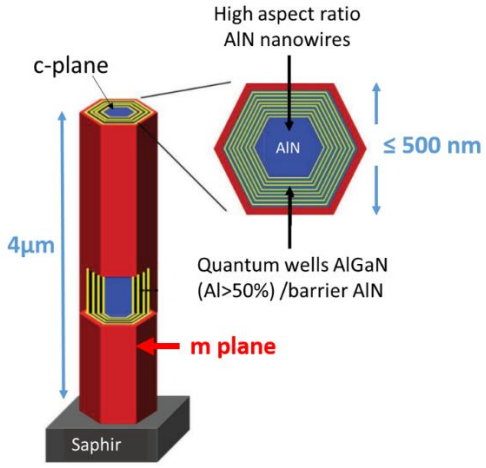

Fig. 2 AlN nanowires profiles obtained with two diferent carrier wafers. (a) straight profile and no passivation layer using Si CW. (b) tapered profile and passivation layer with Si_3N_4 CW.

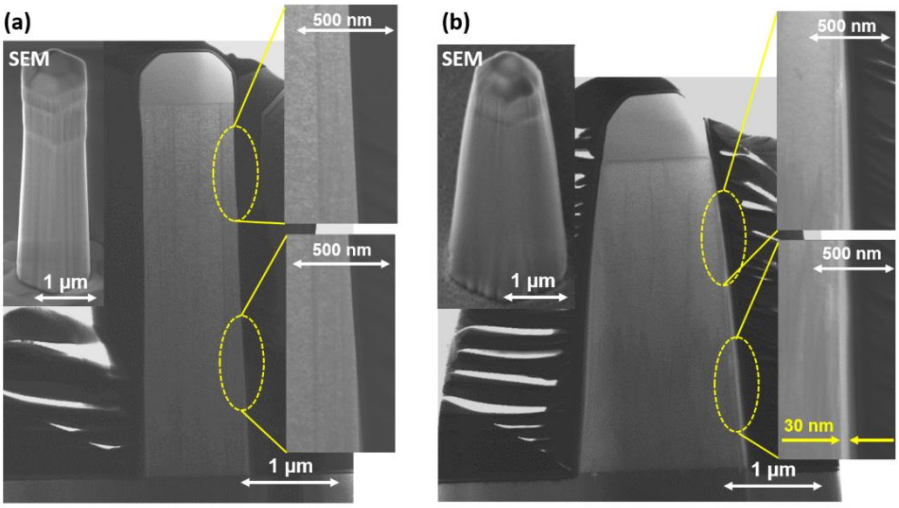

Fig 3. Nanowires profile evolution from tapered to straight or reentrant with source power increasing.